

MSKSEMI

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT

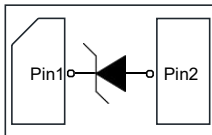


PLED

Product data sheet



DFN1610-2L



Circuit diagram

Marking H7N

Feature

- 1400W Peak pulse power per line ($t_P = 8/20\mu s$)
- DFN1610-2L package
- Response time is typically $< 1\text{ ns}$
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) $\pm 30KV(\text{air}), \pm 30KV(\text{contact});$ IEC 61000-4-4 (EFT) 40A(5/50ns)

Applications

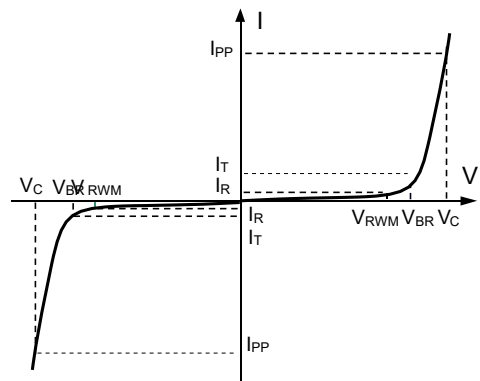
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- Lead finish: 100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature: $260^\circ C$
- Pure tin plating: $7 \sim 17\ \mu m$
- Pin flatness: $\leq 3\text{mil}$
- Device meets MSL3 requirements

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}				7	V
Breakdown Voltage	V_{BR}	$I_t = 1\text{mA}$		8	9.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 7\text{V}$			1	μA
Clamping Voltage	V_C	$I_{PP} = 70\text{A}$ $t_P = 8/20\mu\text{s}$		20	24	V
Junction Capacitance	C_j	$V_R = 0\text{V}$ $f = 1\text{MHz}$	650	700	750	pF

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power ($t_P = 8/20\mu\text{s}$)	P_{pp}	1400	W
Lead Soldering Temperature	T_L	260 (10 sec)	°C
Operating Temperature	T_J	-55 to +125	°C
Storage Temperature	T_{STG}	-55 to +150	°C

Typical Characteristics

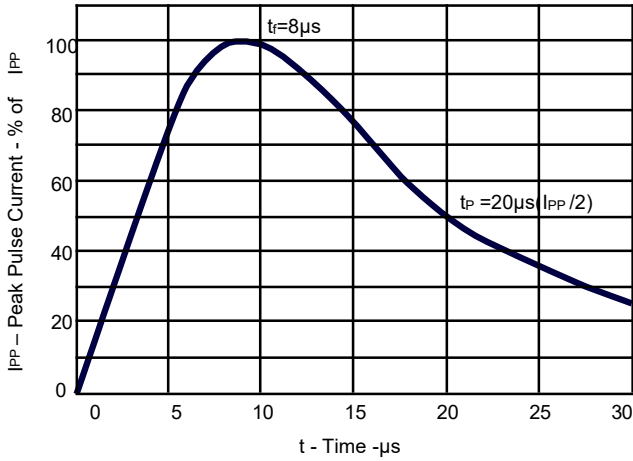


Fig 1. Pulse Waveform

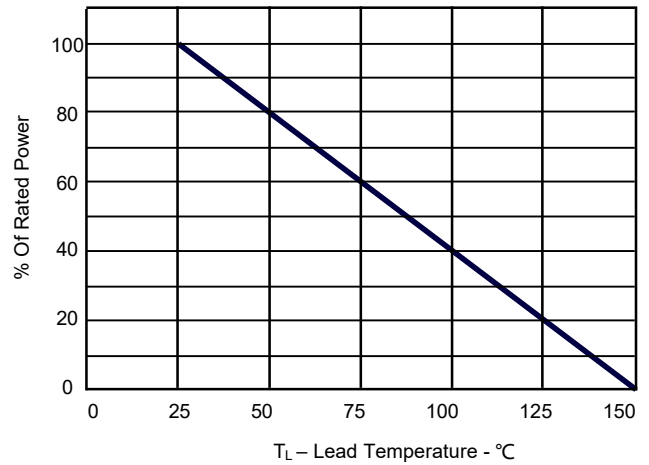


Fig 2. Power Derating Curve

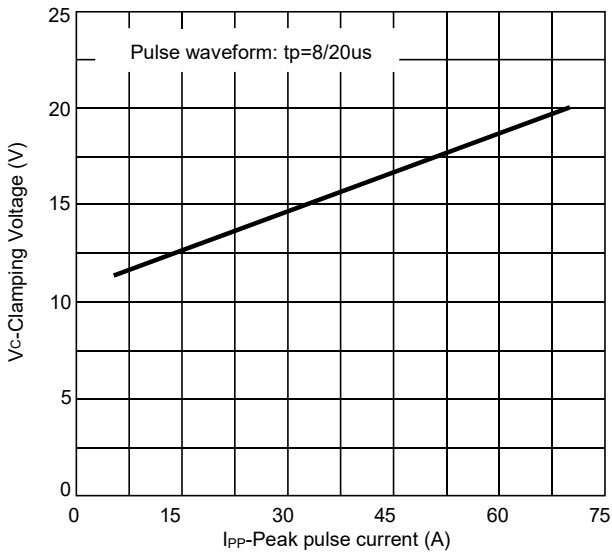


Fig 3. Clamping voltage vs. Peak pulse current

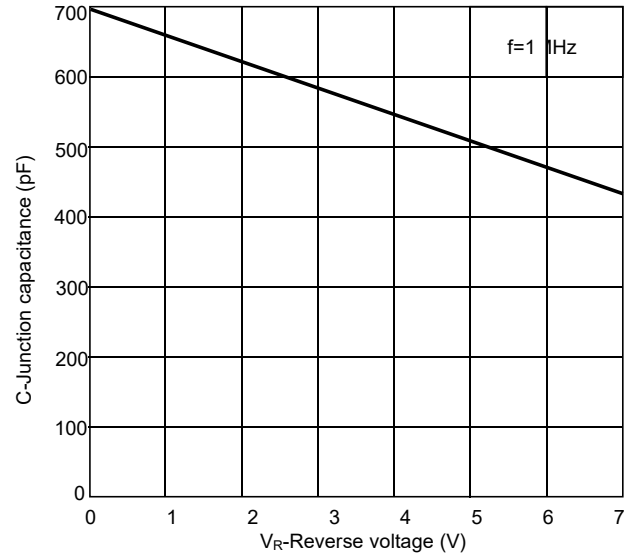


Fig 4. Capacitance vs. Revers voltage

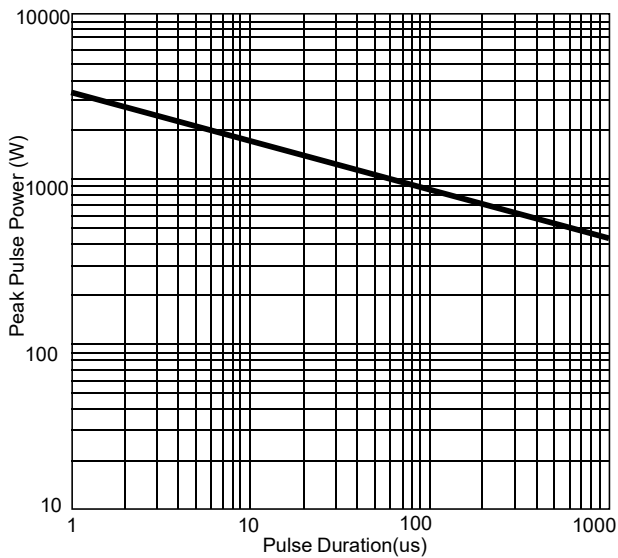
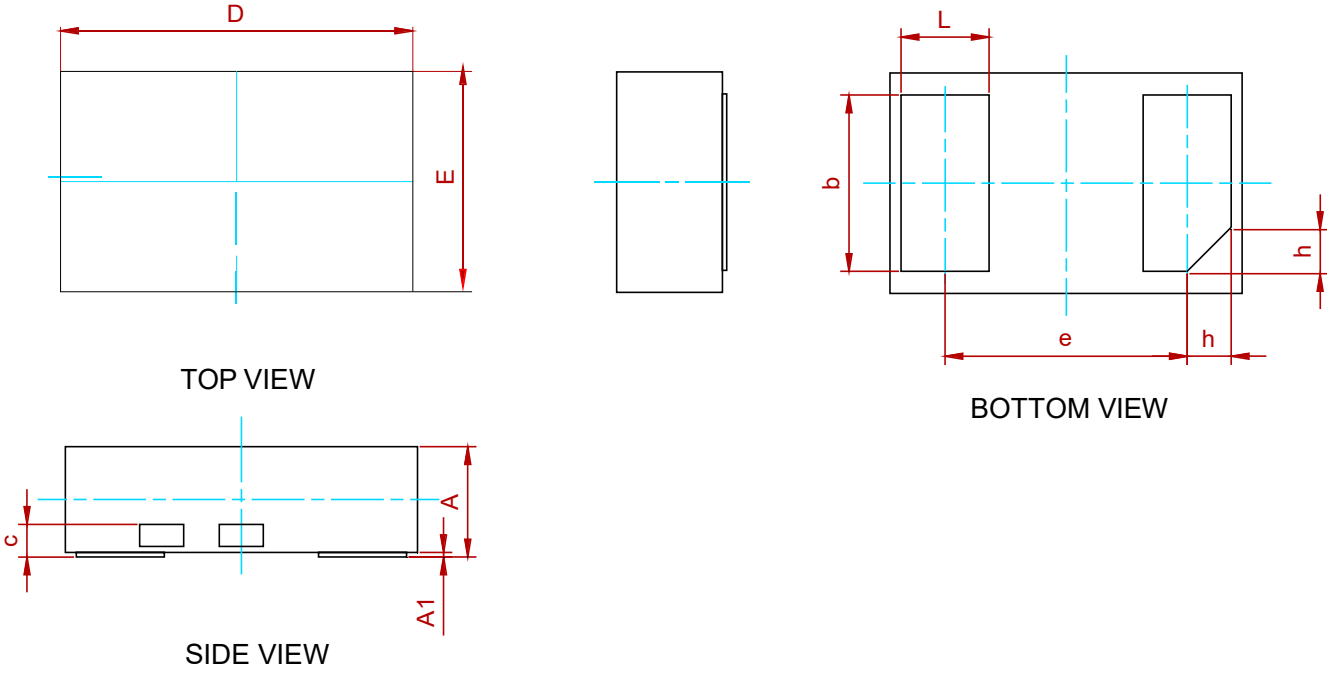


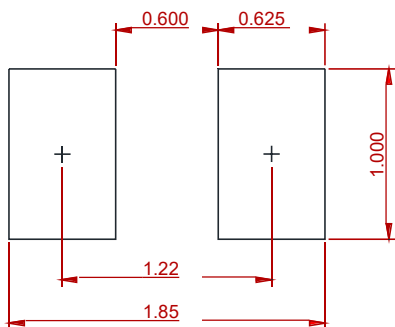
Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

PACKAGE MECHANICAL DATA



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.45	0.50	0.55
A1	0.00	0.02	0.05
c	0.15 Ref.		
b	0.75	0.80	0.85
L	0.35	0.40	0.45
D	1.55	1.60	1.65
E	0.95	1.00	1.05
e	1.10 BSC		
h	0.20 Ref.		

Recommend PCB Layout (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

REEL SPECIFICATION

P/N	PKG	QTY
PTVSHC2EN7VU-MS	DFN1610-2L	3000

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